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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/625,277	07/23/2003	Dong-Sauk Kim	29926/39495	8394
4743	7590	06/30/2005	EXAMINER	
MARSHALL, GERSTEIN & BORUN LLP 233 S. WACKER DRIVE, SUITE 6300 SEARS TOWER CHICAGO, IL 60606			TRAN, THANH Y	
			ART UNIT	PAPER NUMBER
			2822	

DATE MAILED: 06/30/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

## Office Action Summary

Application No.

10/625,277

Applicant(s)

DONG-SAUK KIM

Examiner

Thanh Y. Tran

Art Unit

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --  
**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☒ Responsive to communication(s) filed on 22 April 2005.  
2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.  
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-24 is/are pending in the application.  
4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.  
6) ☒ Claim(s) 1-6, 12 and 18 is/are rejected.  
7) ☒ Claim(s) 7-11, 13-17 and 19-24 is/are objected to.  
8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.  
10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

### Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☒ All b) ☐ Some \* c) ☐ None of:  
1. ☒ Certified copies of the priority documents have been received.  
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

### Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)  
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)  
3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date 7/23/03 & 2/4/05  
4) ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date. \_\_\_\_\_  
5) ☐ Notice of Informal Patent Application (PTO-152)  
6) ☐ Other: \_\_\_\_\_

### DETAILED ACTION

Applicant's election with traverse of Species II (Fig. 9) filed 04/22/05 has been fully considered and is persuasive. The previous election/restrictions requirement is hereby withdrawn.

#### *Claim Rejections - 35 USC § 103*

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1-6, 12 and 18 are rejected under 35 U.S.C. 103(a) as being unpatentable over the admitted prior art (figure 4) in view of Kaeriyama (U.S. 6,150,214).

As to claims 1 and 12, the admitted prior art (figure 4) discloses a semiconductor device and a corresponding method, comprising: a plurality of capacitor plugs (41) formed within a predetermined interval interleaved between two bit lines (40) and midpoints of capacitor plugs (41) are located at inter-section points of X axis virtual line (X1, X2) and Y axis virtual line (Y1, Y2), wherein the X axis virtual lines (X1, X2) are parallel with the bit lines (40) and the Y axis virtual lines (Y1, Y2) are perpendicular to the X axis virtual lines (X1, X2); and a plurality of lower electrodes (42, 42A, 42B) of capacitors formed within a predetermined interval to be respectively connected with the capacitor plugs (41) in one to one correspondence.

The admitted prior art (figure 4) does not disclose each lower electrode is circularly shaped.

Kaeriyama discloses in figure 4 a semiconductor device wherein each lower electrode ("capacitor plate" 16) is circularly shaped. Therefore, it would have been obvious to a person having ordinary skill in the art at the time the invention was made to modify the semiconductor device of the admitted prior art (figure 4) by having each lower electrode which is circularly shaped as taught by Kaeriyama for reducing the critical dimensions of active elements, thus increasing the functionality and performance of the semiconductor device (see col. 1, lines 20-31 in Kaeriyama).

As to claim 2, the admitted prior art (figure 4) discloses a semiconductor device, wherein a lower electrode (42) and neighbored lower electrode (42A) disposed along a direction of Y virtual axis line are formed not to have overlapped area, if one of lower electrode (42) is moved to same X virtual axis line as the other lower electrode (42A or 42B).

As to claim 3, the admitted prior art (figure 4) discloses a semiconductor device, wherein the lower electrode (42) and neighbored lower electrode (42A) disposed along a direction of Y virtual axis (Y1'', Y2'') are not on the same Y virtual axis (Y1'' and Y2'' are not on the same axis).

As to claim 4, the admitted prior art (figure 4) discloses a semiconductor device, wherein the midpoints of the lower electrode (42) and the neighbored lower electrode (42A) are not disposed along the same Y virtual axis (Y1'' and Y2'' are not on the same virtual axis).

As to claim 5, the admitted prior art (figure 4) discloses a semiconductor device, wherein a ratio of a major axis (X1, Y1''; and X1, Y1) to a minor axis (X1, Y2''; and X1, Y2) of the upper plane of the lower electrodes (42, 42A) ranges from about 1 to 1.

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As to claim 6, the admitted prior art (figure 4) discloses a semiconductor device, wherein an area of an upper plane of the lower electrode (42, 42A) is practically identical to that of an lower plane of the lower electrode (lower electrodes 42B) in view of a three-dimensional structure and the lower electrode having a lateral plane (a lateral plane is the intermediate bit line 40 positioned between the upper and lower planes of the electrodes) which connects the upper plane with the lower plane, wherein the lateral plane is substantially vertical to the upper plane and lower plane respectively.

The admitted prior art (figure 4) does not disclose and the lower electrode features a circular cylinder structure.

Kaeriyama discloses in figure 4 a semiconductor device wherein the lower electrode ("capacitor plate" 16) features a circular cylinder structure. Therefore, it would have been obvious to a person having ordinary skill in the art at the time the invention was made to modify the semiconductor device of the admitted prior art (figure 4) by having a lower electrode that features a circular cylinder structure as taught by Kaeriyama for reducing the critical dimensions of active elements, thus increasing the functionality and performance of the semiconductor device (see col. 1, lines 20-31 in Kaeriyama).

As to claim 18, the admitted prior art (figure 4) discloses a semiconductor device and a corresponding method, wherein an area of an upper plane of the lower electrode (42, 42A) is practically identical to that of an lower plane of the lower electrode (lower electrodes 42B) and the lower electrode having a lateral plane (a lateral plane is the intermediate bit line 40 positioned between the upper and lower planes of the electrodes) which connects the upper plane with the lower plane and practically vertical to the upper plane and lower plane.

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The admitted prior art (figure 4) does not disclose and the lower electrode has a circular cylinder structure.

Kaeriyama discloses in figure 4 a semiconductor device wherein the lower electrode ("capacitor plate" 16) has a circular cylinder structure. Therefore, it would have been obvious to a person having ordinary skill in the art at the time the invention was made to modify the semiconductor device of the admitted prior art (figure 4) by having a lower electrode that has a circular cylinder structure as taught by Kaeriyama for reducing the critical dimensions of active elements, thus increasing the functionality and performance of the semiconductor device (see col. 1, lines 20-31 in Kaeriyama).

***Allowable Subject Matter***

3. Claims 7-11, 13-17 and 19-24 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

***Conclusion***

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Cho et al (U.S. 6,242,332) discloses method for forming self-aligned contact.

**Contact Information**


Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh Y. Tran whose telephone number is (571) 272-2110. The examiner can normally be reached on M-F (9-6:30pm).

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TYT

  
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